

## CORRECTION

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## Correction: 'Stateful' threshold switching for neuromorphic learning

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Correction for "Stateful' threshold switching for neuromorphic learning' by Zhijian Zhong et al., *Nanoscale*, 2022, DOI: [10.1039/d1nr05502j](https://doi.org/10.1039/d1nr05502j).

The authors regret that the last sentence of the second paragraph in the [Results and discussion] section, [Emulating associative learning *via* 'stateful' TA] subsection, contained errors. The correct sentence is the following:

"Naturally, high efficiency to build this acquisition can be reached if a larger  $V_{US}$  is applied, upon which only one training cycle is required with a  $V_{US}$  pulse of over 1.2 V (Fig. S8 in the ESI†)."

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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